

Jan. 10, 2005

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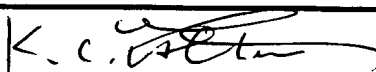
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application Number	10/506,478
		Filing Date	September 1, 2004
		First Named Inventor	Hyosang KANG
		Art Unit	Not yet assigned.
		Examiner Name	Not yet assigned.
(Use as many sheets as necessary)		Attorney Docket Number	61282.00016
Sheet	1	of	1

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
KCC	1.	CHO, Byeong-Ok. <i>et al.</i> , "Angular Dependence of the Redeposition Rates During SiO <sub>2</sub> Etching in a CF <sub>4</sub> Plasma" J. Vac. Sci. Technol. A 19(3) May/Jun 2001, pp. 730-735.	
	2.	LEE, Gyeo-Re <i>et al.</i> , "Sidewall-angle Effect on the Bottom Etch Profile in SiO <sub>2</sub> Etching Using a CF <sub>4</sub> Plasma" J. Vac. Sci. Technol. B 19(1), Jan/Feb 2001, pp. 172-178.	
	3.	MIN, Jae-Ho, <i>et al.</i> , "Reseposition of Etch Products on Sidewalls During SiO <sub>2</sub> Etching in a Fluorocarbon Plasma. III. Effects of O <sub>2</sub> Addition to CF <sub>4</sub> Plasma" J. Vac. Sci. Technol. B21(4) Jul/Aug 2003 American Vacuum Society, pp. 1210-1215.	
	4.	PINTA, R. <i>et al.</i> , "Reactive Etching in SF <sub>6</sub> /Gs Mixtures" InP Misfet Technology Vol. 134, No. 1, January 1987, pp. 165-175.	
KCC	5.	ZAROWIN, C.B. "Plasma Etch Anisotropy - Theory and Some Verifying Experiments Relating Ion Transport, Ion Energy, and Etch Profiles" J. Electrochem. Soc.: Solid state Science and Technology, May, 1983, pp. 1144-1152.	

Examiner Signature		Date Considered	4/14/06
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